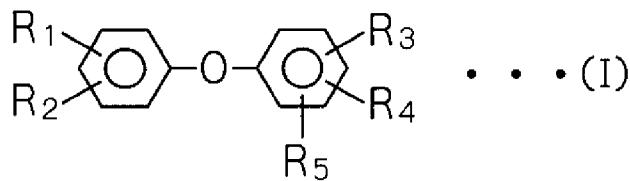


LISTING OF CLAIMS

1. **(Currently amended)** A developer composition for positive resists, comprising an organic quaternary ammonium base as a main component a novolak resin and a naphthoquinone diazide compound, 2 to 5% by mass of tetramethylammonium hydroxide and a surfactant in an aqueous solution,

 said surfactant containing an anionic surfactant represented by the following general formula (I):



 wherein at least one member of R₁ and R₂ represents an alkyl or alkoxy group having 5 to 18 carbon atoms and any remaining member represents a hydrogen atom, or an alkyl or alkoxy group having 5 to 18 carbon atoms, and at least one member of R₃, R₄ and R₅ represents a group represented by the following general formula (II):



 wherein M represents a metal atom selected from the group consisting of sodium, potassium, and calcium, and any remaining member represent a hydrogen atom or a group represented by the above general formula (II), provided that, in the general formula (I), when two or more groups represented by the general formula (II) are present, M may be the same or different, and wherein

the amount of said anionic surfactant is in the range of 1,000 to 50,000 ppm based on said developer composition.

2. **(Canceled)**

3. **(Previously presented)** A method for formation of a resist pattern, comprising applying a resist composition on a substrate to form a resist layer, prebaking the resist layer, selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to claim 1 to form a resist pattern.

4. **(Previously presented)** A method for formation of a resist pattern, comprising applying a resist composition on a substrate to form a resist layer, prebaking the resist layer,

selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to claim 2 to form a resist pattern.